



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **MIMINO, Yutaka et al.**

Serial No.: 10/090,610

Filed: **March 6, 2002**

Group Art Unit: **2818**

Examiner: **T. HO**

P.T.O. Confirmation No.: **4961**

For: **HIGH FREQUENCY SEMICONDUCTOR DEVICE**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

April 14, 2003

Sir:

In response to the Office Action dated **January 15, 2003**, please amend the above identified application as follows:

IN THE CLAIMS:

CANCEL claim 2.

AMEND claim 1 to read as follows:

1. A multilayer wiring structure for semiconductor devices, comprising:
- a semiconductor substrate;
 - at least one active region supplied with an electric power from a power-supply potential;
 - a plurality of power-supply lines for supplying with the electric power to said active region therethrough, said power-supply lines disposed at different layers of the multilayer wiring structure on said semiconductor substrate and being connected in parallel to each other; and
 - a common power-supply line provided between said power-supply potential and said active

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